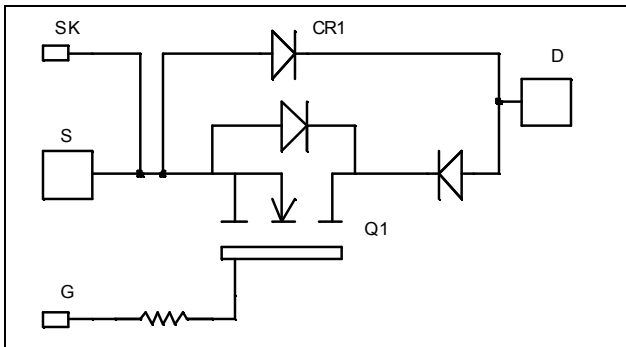


*Single switch  
Series & parallel diodes  
MOSFET Power Module*

$V_{DSS} = 1200V$   
 $R_{DSon} = 100m\Omega$  typ @  $T_j = 25^\circ C$   
 $I_D = 116A$  @  $T_c = 25^\circ C$

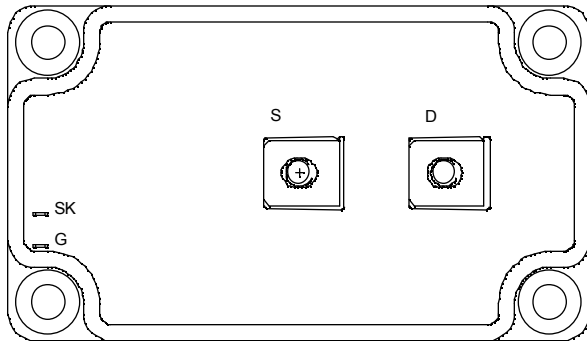


### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Power MOS 7<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration
- AlN substrate for MOSFET improved thermal performance



### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	1200	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	116
		$T_c = 80^\circ C$	86
$I_{DM}$	Pulsed Drain current	464	A
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	120	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	3290
$I_{AR}$	Avalanche current (repetitive and non repetitive)	24	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	3200	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 1200\text{V}$			1	mA
		$V_{GS} = 0\text{V}, V_{DS} = 1000\text{V}$			3	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 58\text{A}$		100	120	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 20\text{mA}$	3		5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$			$\pm 400$	nA

**Dynamic Characteristics**

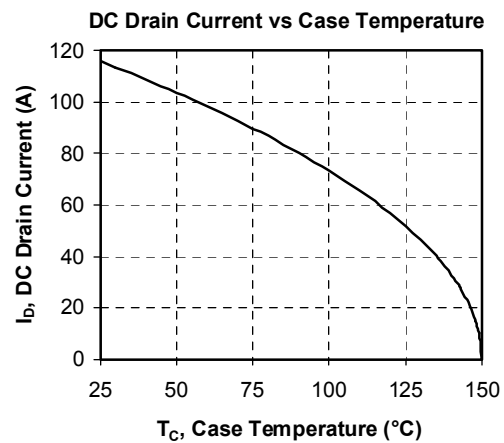
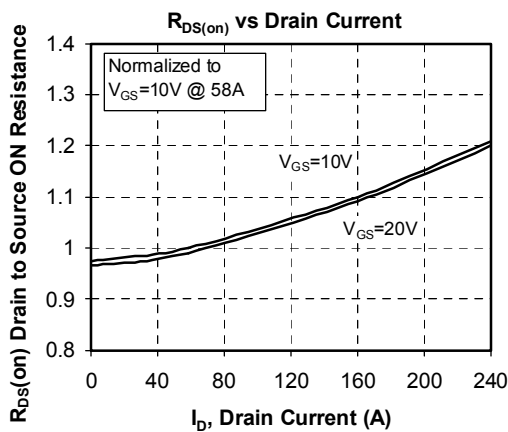
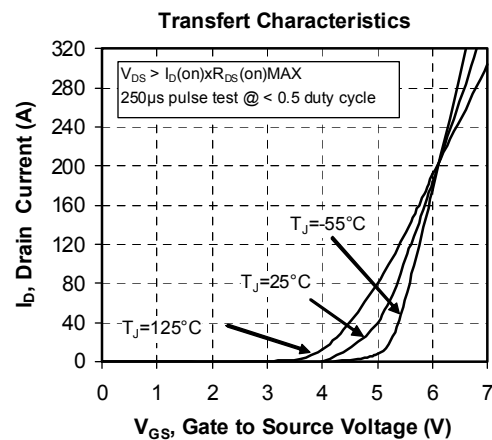
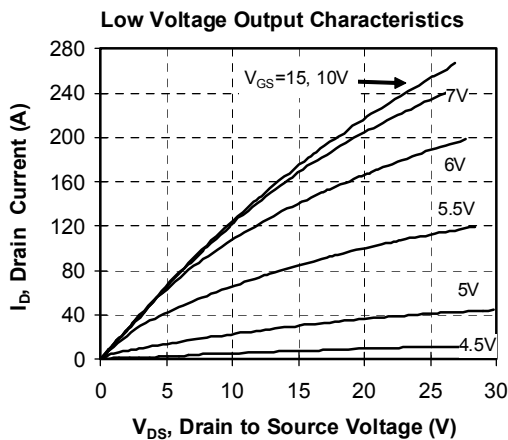
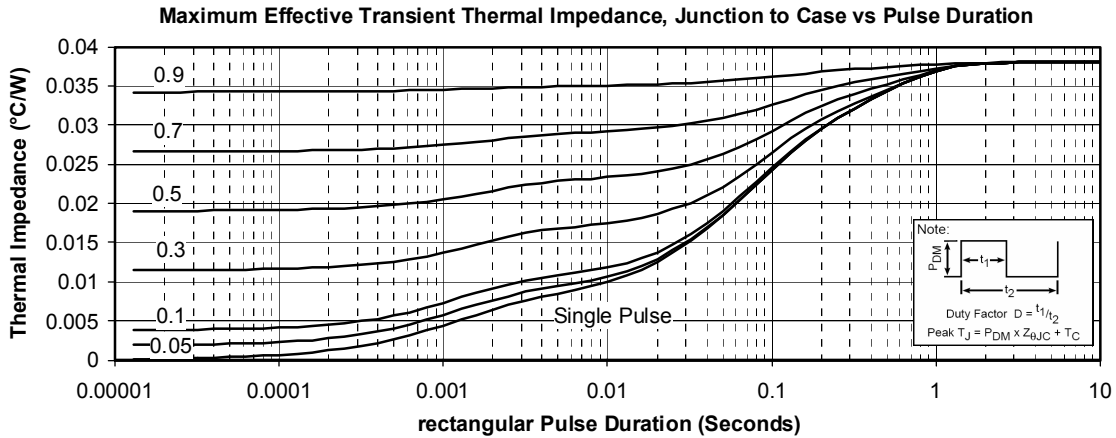
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$		28.9		nF
$C_{oss}$	Output Capacitance	$V_{DS} = 25\text{V}$		4.4		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.8		
$Q_g$	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 600\text{V}$ $I_D = 116\text{A}$		1100		nC
$Q_{gs}$	Gate – Source Charge			128		
$Q_{gd}$	Gate – Drain Charge			716		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching @ 125°C</b> $V_{GS} = 15\text{V}$ $V_{Bus} = 800\text{V}$ $I_D = 116\text{A}$ $R_G = 1.2\Omega$		20		ns
$T_r$	Rise Time			17		
$T_{d(off)}$	Turn-off Delay Time			245		
$T_f$	Fall Time			62		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ 25°C</b> $V_{GS} = 15\text{V}, V_{Bus} = 800\text{V}$ $I_D = 116\text{A}, R_G = 1.2\Omega$		5		mJ
$E_{off}$	Turn-off Switching Energy			4.6		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ 125°C</b> $V_{GS} = 15\text{V}, V_{Bus} = 800\text{V}$ $I_D = 116\text{A}, R_G = 1.2\Omega$		9.2		mJ
$E_{off}$	Turn-off Switching Energy			5.6		

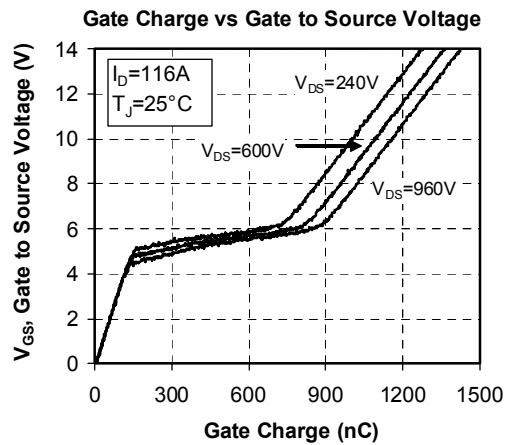
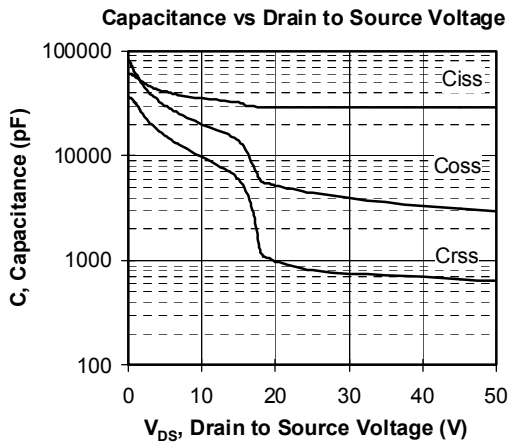
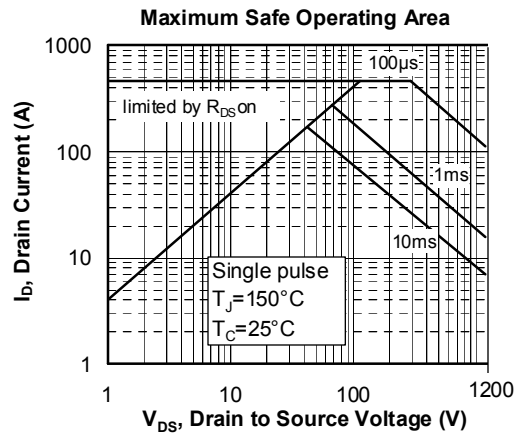
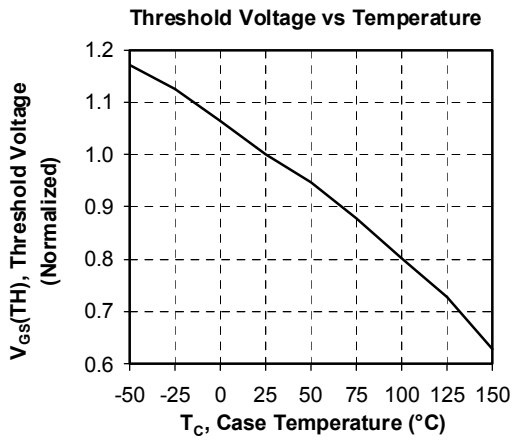
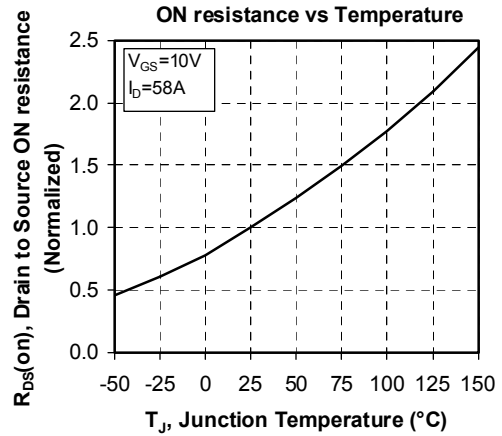
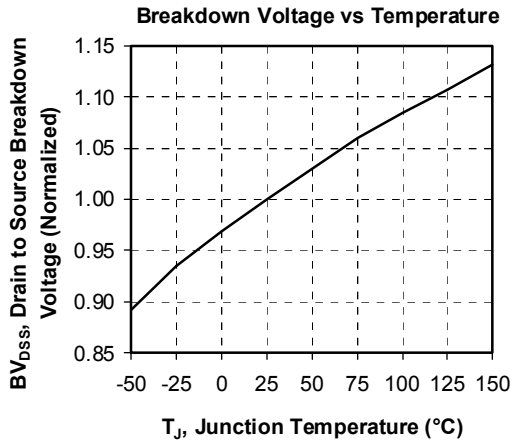
**Series diode ratings and characteristics**

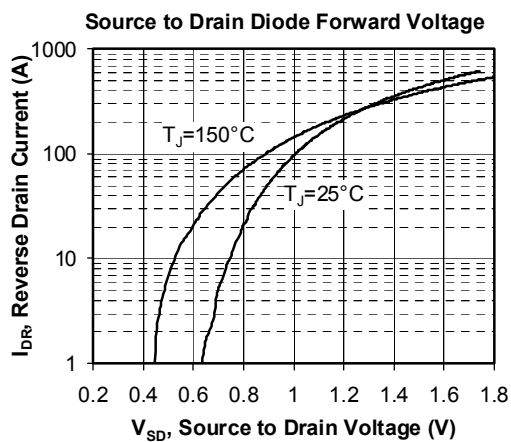
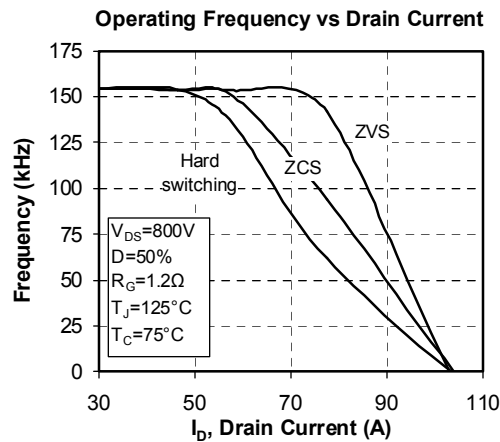
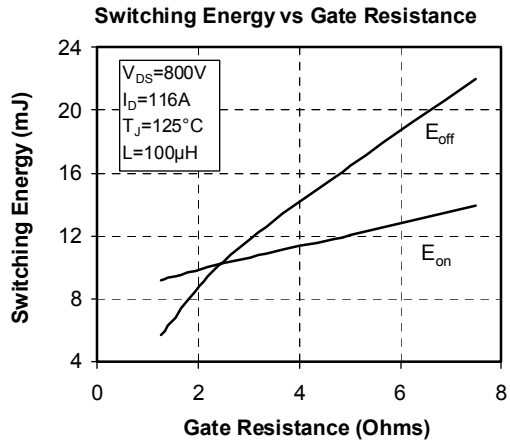
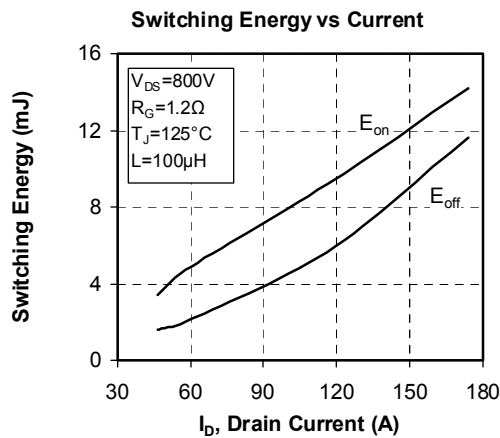
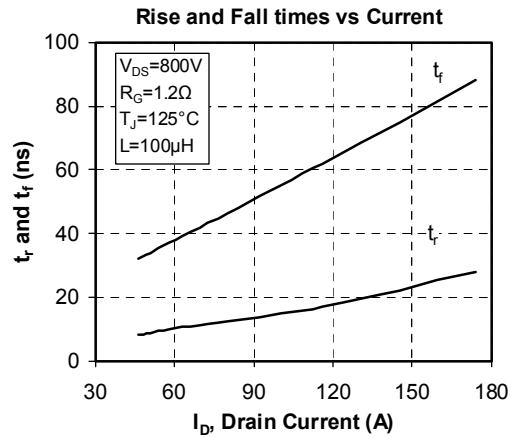
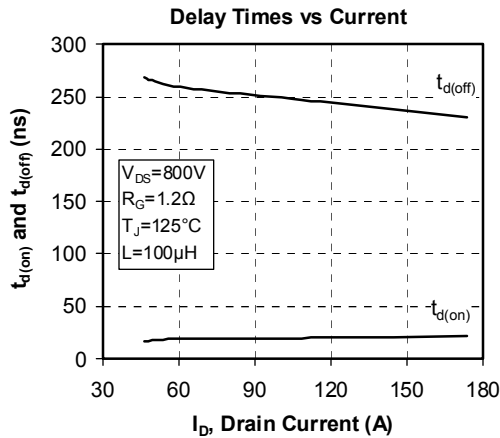
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 200\text{V}$	$T_j = 25^\circ\text{C}$		350	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		600	
$I_F$	DC Forward Current	$T_c = 80^\circ\text{C}$		120		A
$V_F$	Diode Forward Voltage	$I_F = 120\text{A}$		1.1	1.15	V
		$I_F = 240\text{A}$		1.4		
		$I_F = 120\text{A}$	$T_j = 125^\circ\text{C}$		0.9	
$t_{rr}$	Reverse Recovery Time	$I_F = 120\text{A}$ $V_R = 133\text{V}$ $di/dt = 400\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		31	ns
			$T_j = 125^\circ\text{C}$		60	
$Q_{rr}$	Reverse Recovery Charge	$I_F = 120\text{A}$ $V_R = 133\text{V}$ $di/dt = 400\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		120	nC
			$T_j = 125^\circ\text{C}$		500	



## Typical Performance Curve







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